/ Revised record

F	2017-4				
G	2019-11-11	2	V_{CBO} V_{CEO} V_{EBO} I_{CEO}		
H	2020-5-21	1			
A	2022-2-9	all	BR Q AEC-Q101 H Q 245±5℃ 5±0.5sec 255±5℃ 5±0.5sec		

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

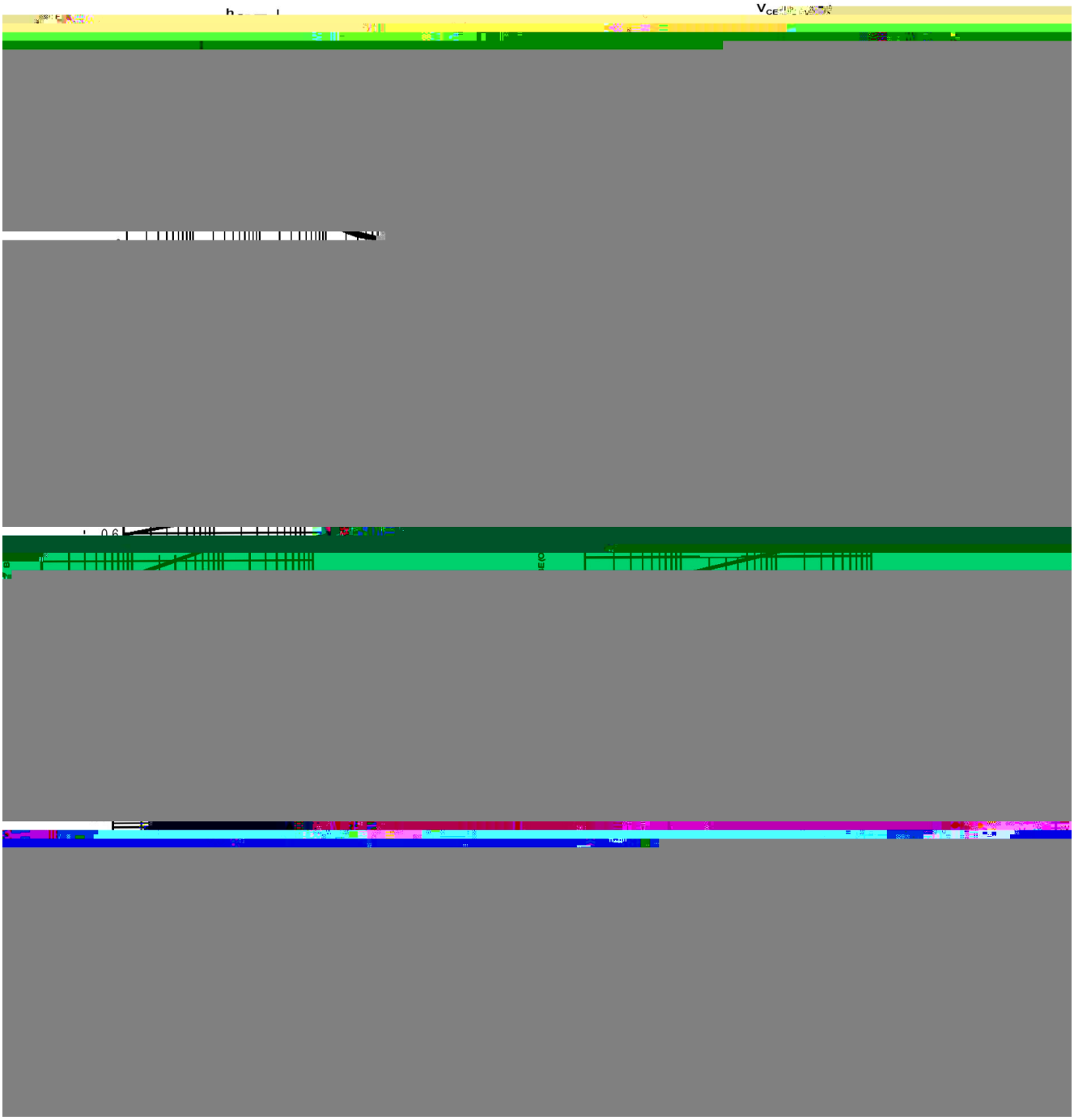
, BRMMBT5551Q AEC-Q101

High voltage, c

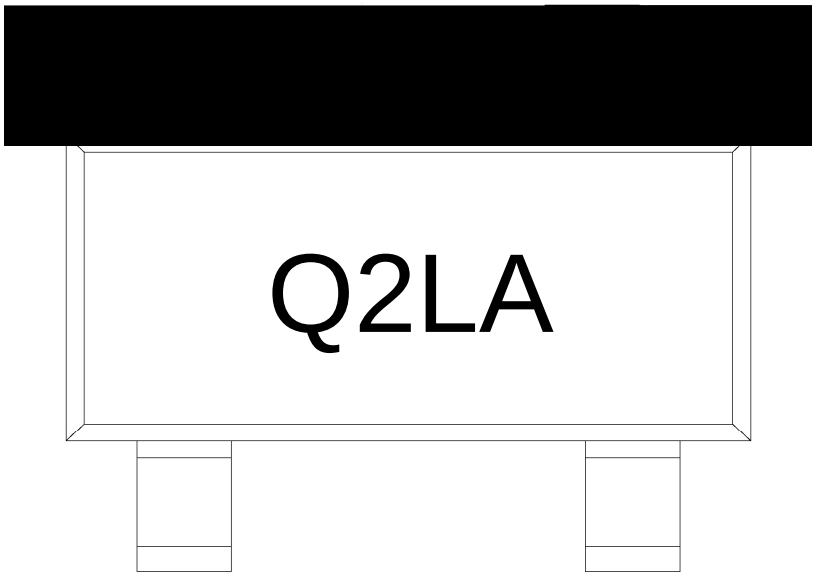
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-600	mA
Base Current	I_B	-300	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	[redacted]	

Parameter	Symbol	Test Conditions

/ Electrical Characteristic Curve



/ Marking Instructions



Q

2L

A h_{FE}

Note:

Q: Automobile halogen-free product Code

2L Product Type Code

A h_{FE} Classifications Symbol Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1	150	200	60	120sec;	1.Preheating:150~200℃, Time:60~120sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5℃, Duration:5±0.5sec.
3		2	10℃/sec.		3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃	10±1 sec.	Temp.:260±5	Time:10±1 sec